

最终数据手册

英飞凌 CoolSiC™ 1200 V 碳化硅沟道 MOSFET

特性

- $T_{vj} = -55 \dots 175^\circ\text{C}$ 时 $V_{DSS} = 1200\text{ V}$
- $T_C = 25^\circ\text{C}$ 时 $I_{DDC} = 69\text{ A}$
- 新的性能优化芯片技术 (Gen1p), 改善了 $R_{DS(on)} \cdot A$ FOM
- 提高了建议开启电压 ($V_{GS(on)} = 20\text{ V}$) 以降低 $R_{DS(on)}$
- 业界领先的开关能量特性, 可降低开关损耗并减少冷却需求
- 最低的器件电容值, 可实现更高的开关速度和更高的功率密度
- 低 C_{rSS}/C_{iSS} 电容比值和高 $V_{GS(th)}$ 的组合, 可避免寄生导通并实现单极性栅极驱动
- 降低了总栅极电荷 Q_{Gtot} , 可降低驱动功率和损耗
- .XT 芯片粘接技术, 实现业界领先的热性能
- 用于优化开关性能的检测引脚
- 最小爬电距离为 7.07 毫米, 以满足高压要求



- Halogen-free
- Green
- Lead-free
- RoHS
- AEC-Q100/101 Qualified

潜在应用

- 车载充电器
- 直流/直流转换器
- 辅助驱动

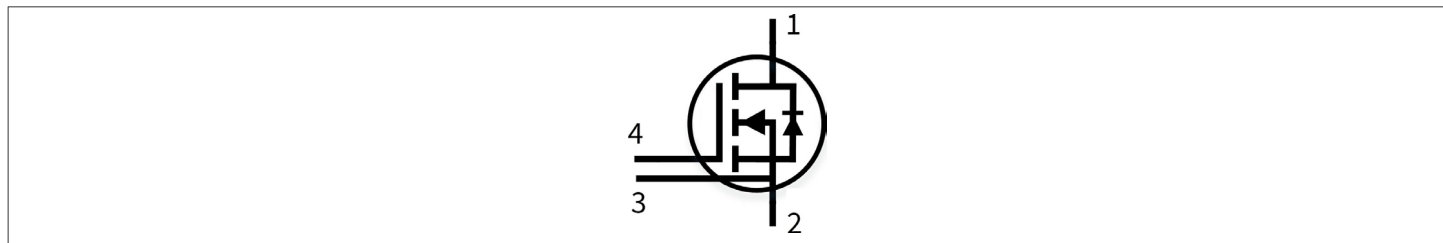
产品验证

- 适合汽车应用。根据 AEC-Q100/101 进行产品验证

描述

引脚定义:

- 1 - 漏极
- 2 - 来源
- 3 - 开尔文检测
- 4 - 栅极



Type	Package	Marking
AIMZHN120R030M1T	PG-TO247-4-U05	A12M1N030

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1 封装

1 封装

表 1 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}				260	°C
MOSFET/body diode thermal resistance, junction-case ¹⁾	$R_{th(j-c)}$			0.35	0.46	K/W

1) 未经过生产测试。该参数已通过设计/特性验证

2 MOSFET

表 2 最大额定值

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage ¹⁾	V_{DSS}	$T_{vj} = -55...175\text{ °C}$	1200	V	
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$ ²⁾	I_{DCC}	$V_{GS} = 20\text{ V}$	$T_c = 25\text{ °C}$	69	A
			$T_c = 100\text{ °C}$	49	
Peak drain current, t_p limited by $T_{vj(max)}$ ²⁾	I_{DM}	$V_{GS} = 20\text{ V}$	176	A	
Gate-source voltage, max. transient voltage ³⁾	V_{GS}	$t_p \leq 0.5\ \mu\text{s}, D < 0.01$	-10...25	V	
Gate-source voltage, max. static voltage ³⁾	V_{GS}		-5...23	V	
Avalanche energy, single pulse	E_{AS}	$I_D = 20\text{ A}, V_{DD} = 50\text{ V}, L = 1.8\text{ mH}$	361	mJ	
Power dissipation, limited by $T_{vj(max)}$ ²⁾	P_{tot}		$T_c = 25\text{ °C}$	326	W
			$T_c = 100\text{ °C}$	163	

1) 在 $T_{vj}=25\text{ °C}$ 下进行测试，并通过全温度范围内的设计/特性验证

2) 未经过生产测试。该参数已通过设计/特性验证

3) **重要注释：** 正负栅极源电压的选择会影响器件的长期行为。为了确保器件在计划使用寿命内的正常运行，必须考虑应用说明 AN2018-09 中描述的设计指南。

表 3 建议值

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		20	V
Recommended turn-off gate voltage	$V_{GS(off)}$		0	V

表 4 特征值

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 27\text{ A}$	$T_{vj} = 25\text{ °C}$, $V_{GS(on)} = 20\text{ V}$		30	38	mΩ
			$T_{vj} = 100\text{ °C}$, $V_{GS(on)} = 20\text{ V}$		42		
			$T_{vj} = 175\text{ °C}$, $V_{GS(on)} = 20\text{ V}$		60		
			$T_{vj} = 25\text{ °C}$, $V_{GS(on)} = 18\text{ V}$		33		
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 8.6\text{ mA}$, $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20\text{ V}$)	$T_{vj} = 25\text{ °C}$	3.7	4.4	5.1	V
			$T_{vj} = 175\text{ °C}$		3.6		
Zero gate-voltage drain current	I_{DSS}	$V_{DS} = 1200\text{ V}$, $V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.4	26	μA
			$T_{vj} = 175\text{ °C}$		50		
Gate leakage current	I_{GSS}	$V_{DS} = 0\text{ V}$	$V_{GS} = 25\text{ V}$			100	nA
			$V_{GS} = -10\text{ V}$			-100	
Forward transconductance	g_{fs}	$I_D = 27\text{ A}$, $V_{DS} = 20\text{ V}$			16.5		S
Short-circuit withstand time ¹⁾	t_{SC}	$V_{DD} \leq 800\text{ V}$, $V_{DS,peak} < 1200\text{ V}$, $T_{vj(start)} = 25\text{ °C}$, $R_{G,ext} = 2\text{ }\Omega$	$V_{GS(on)} = 20\text{ V}$		1.5		μs
			$V_{GS(on)} = 18\text{ V}$		2		
			$V_{GS(on)} = 15\text{ V}$		2.5		
Internal gate resistance	$R_{G,int}$	$f = 1\text{ MHz}$, $V_{AC} = 25\text{ mV}$			2.6		Ω
Input capacitance	C_{iss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$			1738		pF
Output capacitance	C_{oss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$			82		pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$			4.4		pF
C_{oss} stored energy	E_{oss}	$V_{DS} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$, $V_{AC} = 25\text{ mV}$			34		μJ
Total gate charge	Q_G	$V_{DD} = 800\text{ V}$, $I_D = 27\text{ A}$, $V_{GS} = 0/20\text{ V}$, turn-on pulse			57		nC
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800\text{ V}$, $I_D = 27\text{ A}$, $V_{GS} = 0/20\text{ V}$, turn-on pulse			15		nC
Gate-drain charge	Q_{GD}	$V_{DD} = 800\text{ V}$, $I_D = 27\text{ A}$, $V_{GS} = 0/20\text{ V}$, turn-on pulse			10		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800\text{ V}$, $I_D = 27\text{ A}$, $V_{GS} = 0/20\text{ V}$, $R_{GS(on)} = 2\text{ }\Omega$, $R_{GS(off)} = 2\text{ }\Omega$, $L_\sigma = 33\text{ nH}$	$T_{vj} = 25\text{ °C}$		11		ns
			$T_{vj} = 175\text{ °C}$		11		

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3 体二极管 (MOSFET)

表 4 (续) 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rise time	t_r	$V_{DD} = 800\text{ V}, I_D = 27\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 33\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	9		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	12		
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800\text{ V}, I_D = 27\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 33\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	21		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	22		
Fall time	t_f	$V_{DD} = 800\text{ V}, I_D = 27\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 33\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	10		ns
			$T_{vj} = 175\text{ }^\circ\text{C}$	10		
Turn-on energy	E_{on}	$V_{DD} = 800\text{ V}, I_D = 27\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 33\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	155		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	319		
Turn-off energy	E_{off}	$V_{DD} = 800\text{ V}, I_D = 27\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 33\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	70		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	73		
Total switching energy	E_{tot}	$V_{DD} = 800\text{ V}, I_D = 27\text{ A},$ $V_{GS} = 0/20\text{ V},$ $R_{GS(on)} = 2\ \Omega,$ $R_{GS(off)} = 2\ \Omega, L_\sigma = 33\text{ nH}$	$T_{vj} = 25\text{ }^\circ\text{C}$	225		μJ
			$T_{vj} = 175\text{ }^\circ\text{C}$	392		
Virtual junction temperature	T_{vj}		-55		175	$^\circ\text{C}$

1) 通过设计/特性验证

注: 动态测试电路参见图F。

除非另有规定, 特性均为 $T_{vj} = 25^\circ\text{C}$ 。

3 体二极管 (MOSFET)

表 5 最大额定值

Parameter	Symbol	Note or test condition	Values	Unit	
Drain-source voltage ¹⁾	V_{DSS}	$T_{vj} = -55\dots175\text{ }^\circ\text{C}$	1200	V	
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$ ²⁾	I_{SDC}		$T_c = 25\text{ }^\circ\text{C}$	60	A
			$T_c = 100\text{ }^\circ\text{C}$	36	

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表 5 (续) 最大额定值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Peak reverse drain current, t_p limited by $T_{vj(max)}$ ²⁾	I_{SM}		$V_{GS} = 0 V$	61		A
			$-5 V \leq V_{GS} \leq 0 V,$ $t_p = 0.3 \mu s$	80		
			$-5 \leq V_{GS} \leq 0 V, T_{vj} \leq 175^\circ C;$ $t_p \leq 0.3 ms$ for accumulated conduction time < 5 s or $t_p \leq 1 ms$ for accumulated conduction time < 2.5 s ³⁾	207		

- 1) 在 $T_{vj}=25^\circ C$ 下测试, 通过设计/特性验证
 2) 未经过生产测试。该参数已通过设计/特性验证
 3) t_p 和 I_{sm} 的组合不应导致 $T_{vj(max)} > 175^\circ C$

表 6 特征值

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Drain-source reverse voltage	V_{SD}	$I_{SD} = 27 A$	$T_{vj} = 25^\circ C$		3.9	5	V
			$T_{vj} = 100^\circ C$		3.8		
			$T_{vj} = 175^\circ C$		3.7		
MOSFET forward recovery charge	Q_{fr}	$V_{DD} = 800 V,$ $I_{SD} = 27 A, V_{GS} = 0 V,$ $-di_{SD}/dt = 2000 A/\mu s, Q_{fr}$ includes also Q_C	$T_{vj} = 25^\circ C$		203		nC
			$T_{vj} = 175^\circ C$		508		
MOSFET peak forward recovery current	I_{frm}	$V_{DD} = 800 V,$ $I_{SD} = 27 A, V_{GS} = 0 V,$ $-di_{SD}/dt = 2000 A/\mu s, Q_{fr}$ includes also Q_C	$T_{vj} = 25^\circ C$		18		A
			$T_{vj} = 175^\circ C$		33		
Virtual junction temperature	T_{vj}		-55		175	$^\circ C$	

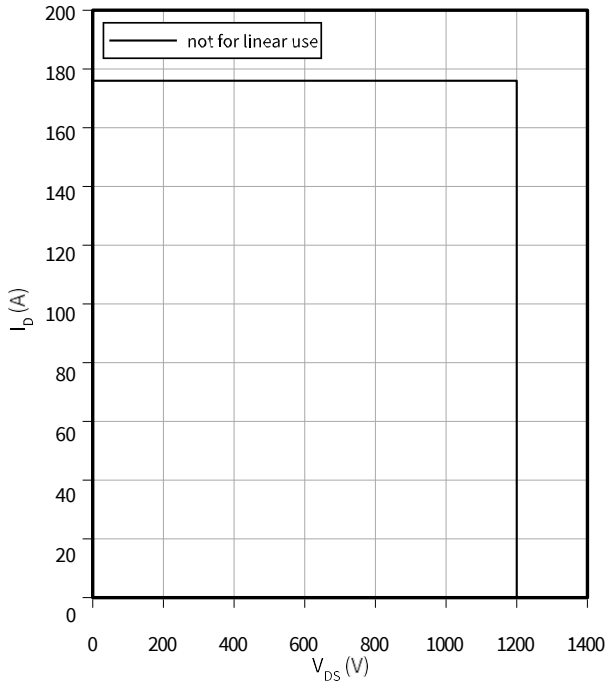
4 特性图

4 特性图

Reverse bias safe operating area (RBSOA)

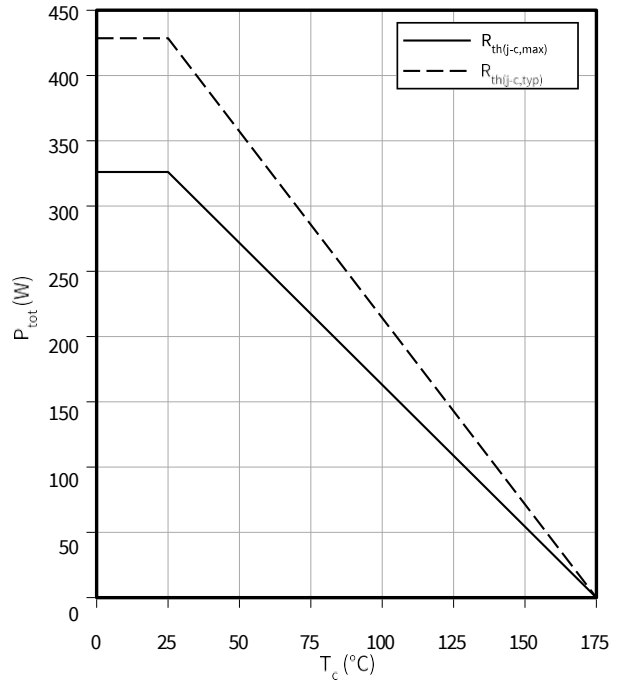
$I_D = f(V_{DS})$

$T_{vj} \leq 175\text{ }^\circ\text{C}$, $V_{GS} = 0/20\text{ V}$, $T_c = 25\text{ }^\circ\text{C}$



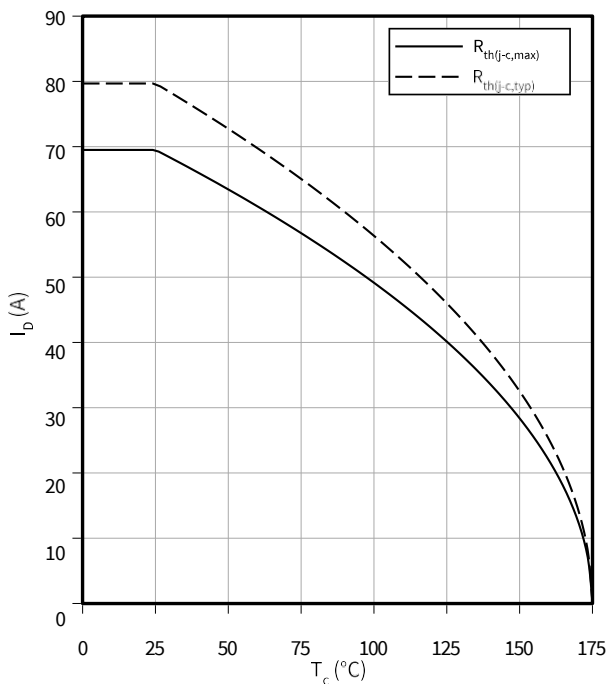
Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$



Maximum DC drain to source current as a function of case temperature

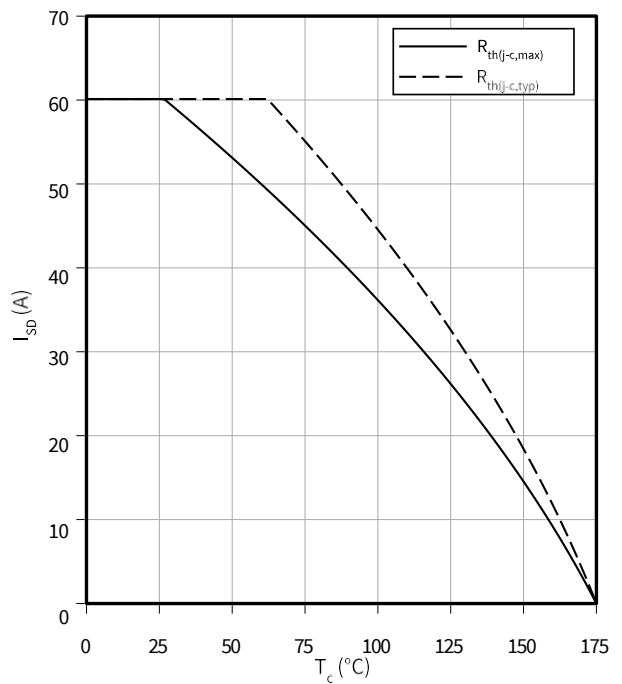
$I_D = f(T_c)$



Maximum source to drain current as a function of case temperature

$I_{SD} = f(T_c)$

$V_{GS} = 0\text{ V}$

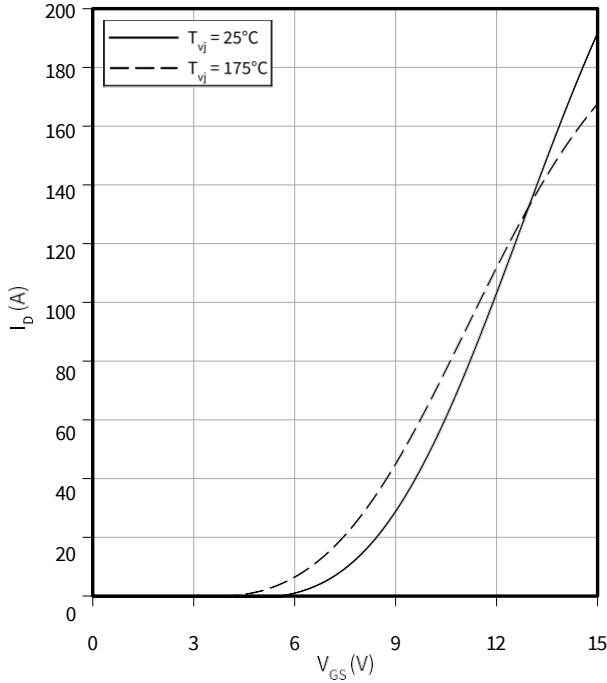


4 特性图

Typical transfer characteristic

$I_D = f(V_{GS})$

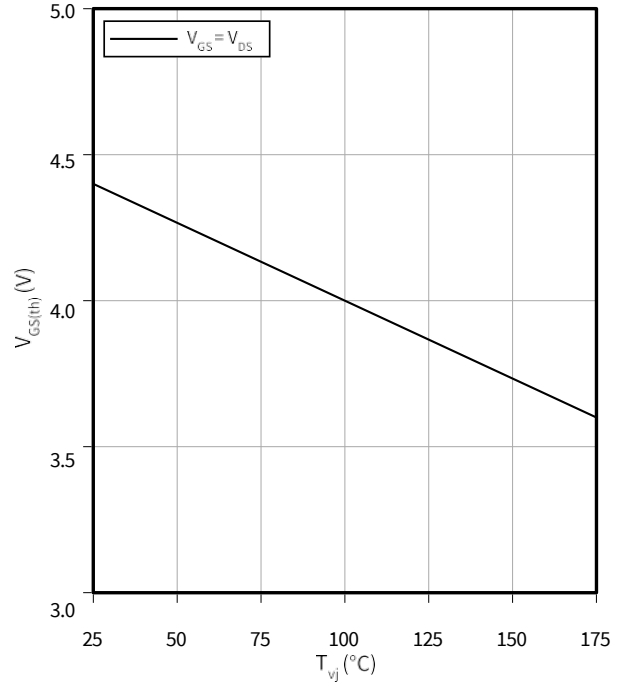
$V_{DS} = 20\text{ V}$, $t_p = 20\ \mu\text{s}$



Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$

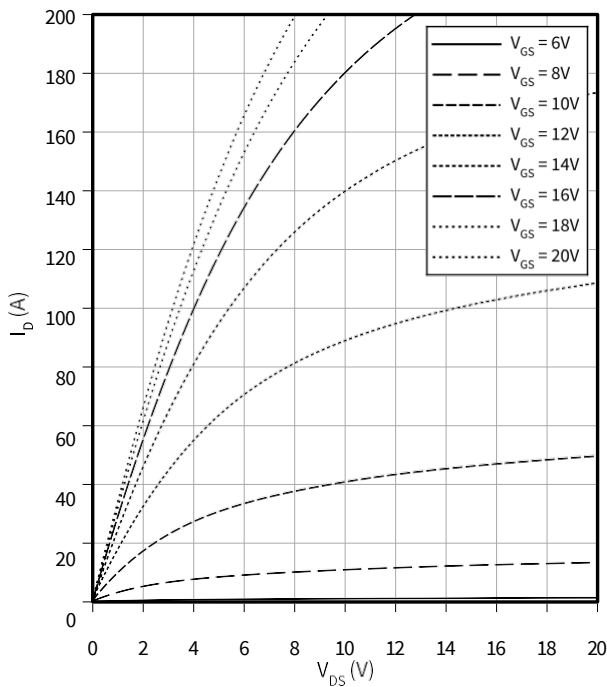
$I_D = 8.6\text{ mA}$



Typical output characteristic, V_{GS} as parameter

$I_D = f(V_{DS})$

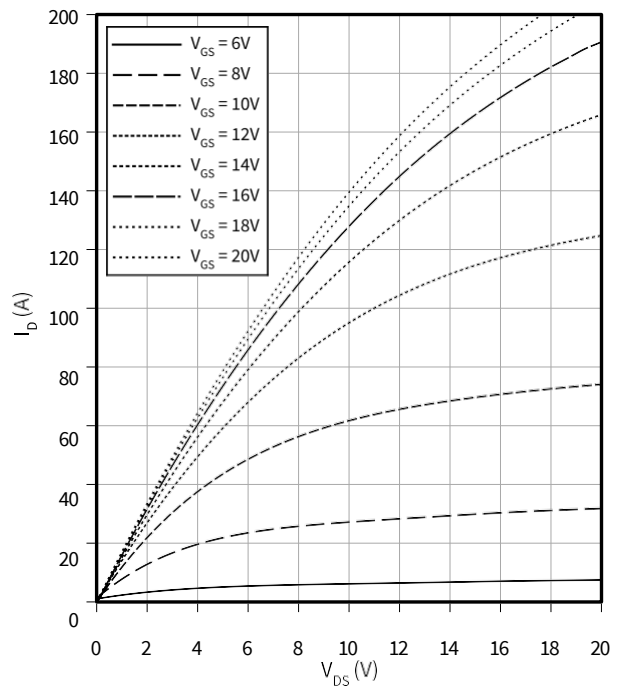
$T_{vj} = 25\ ^\circ\text{C}$, $t_p = 20\ \mu\text{s}$



Typical output characteristic, V_{GS} as parameter

$I_D = f(V_{DS})$

$T_{vj} = 175\ ^\circ\text{C}$, $t_p = 20\ \mu\text{s}$

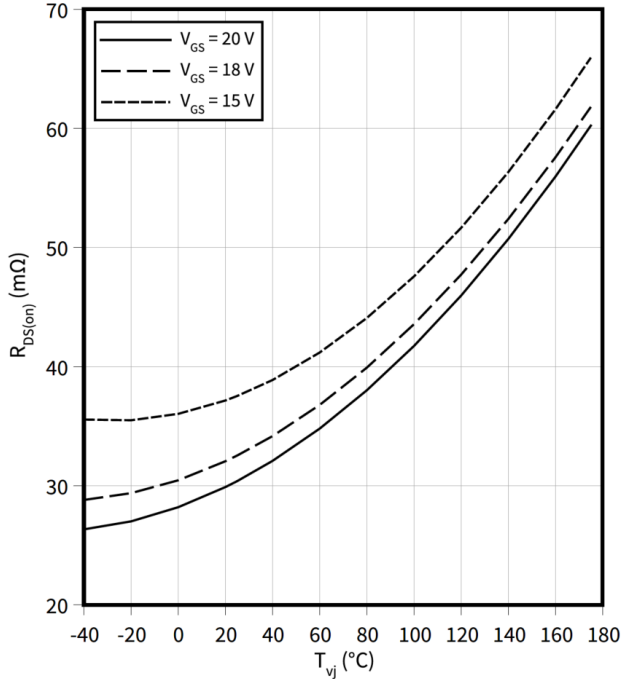


4 特性图

Typical on-state resistance as a function of junction temperature

$R_{DS(on)} = f(T_{vj})$

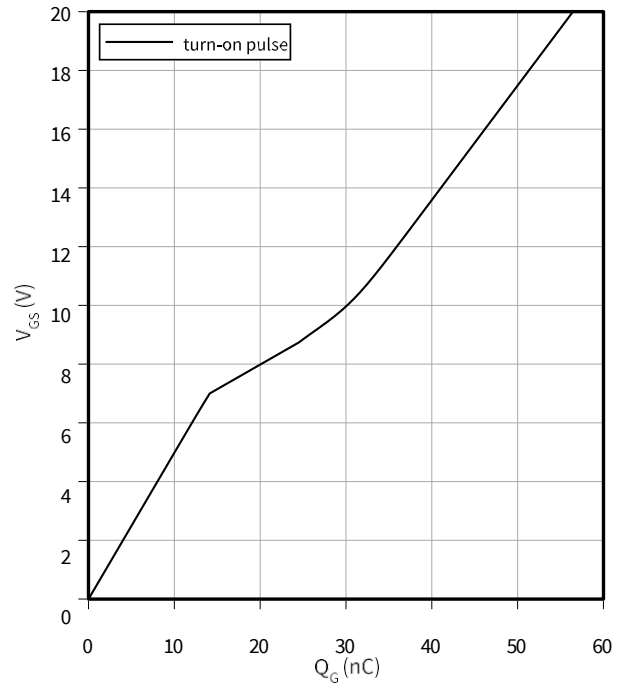
$I_D = 27\text{ A}$



Typical gate charge

$V_{GS} = f(Q_G)$

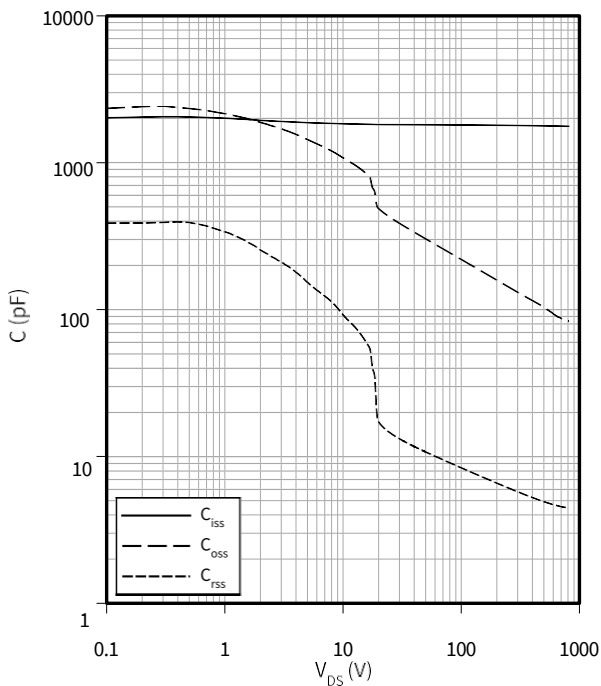
$I_D = 27\text{ A}, V_{DS} = 800\text{ V}$



Typical capacitance as a function of drain-source voltage

$C = f(V_{DS})$

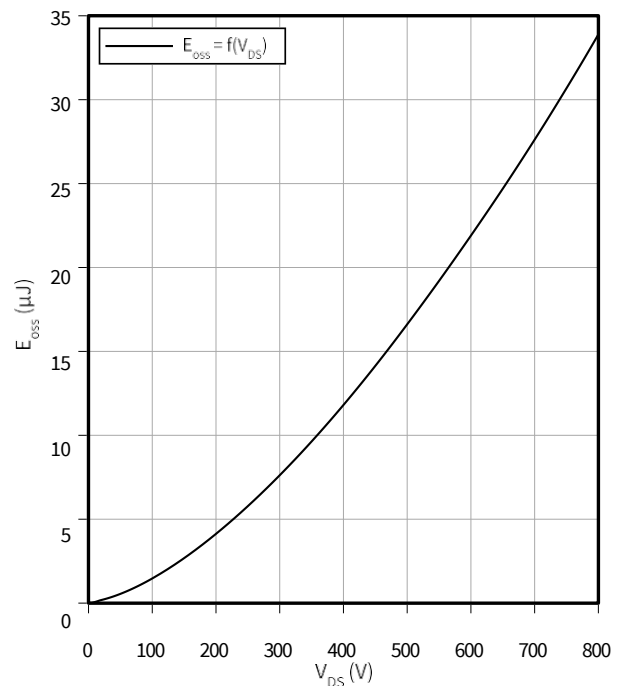
$f = 100\text{ kHz}, V_{GS} = 0\text{ V}$



Typical C_{oss} stored energy

$E_{oss} = f(V_{DS})$

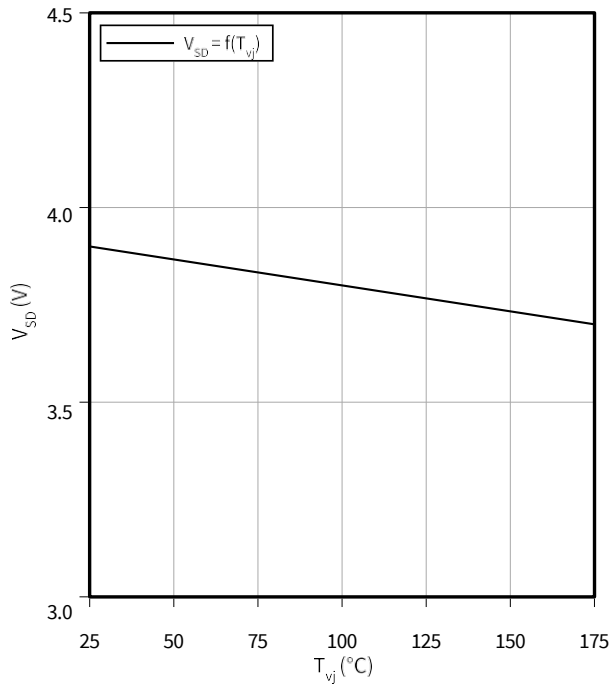
$f = 100\text{ kHz}$



4 特性图

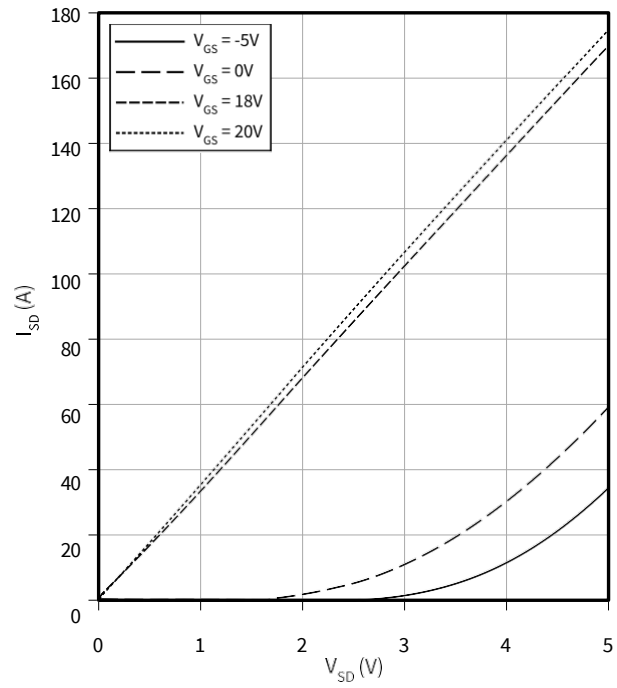
Typical reverse drain voltage as function of junction temperature

$V_{SD} = f(T_{vj})$
 $I_{SD} = 27 \text{ A}, V_{GS} = 0 \text{ V}$



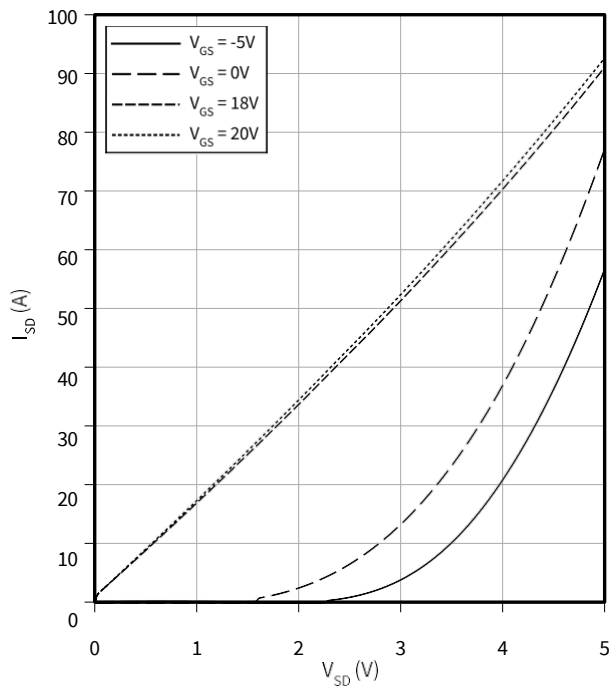
Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 25 \text{ }^\circ\text{C}, t_p = 20 \text{ }\mu\text{s}$



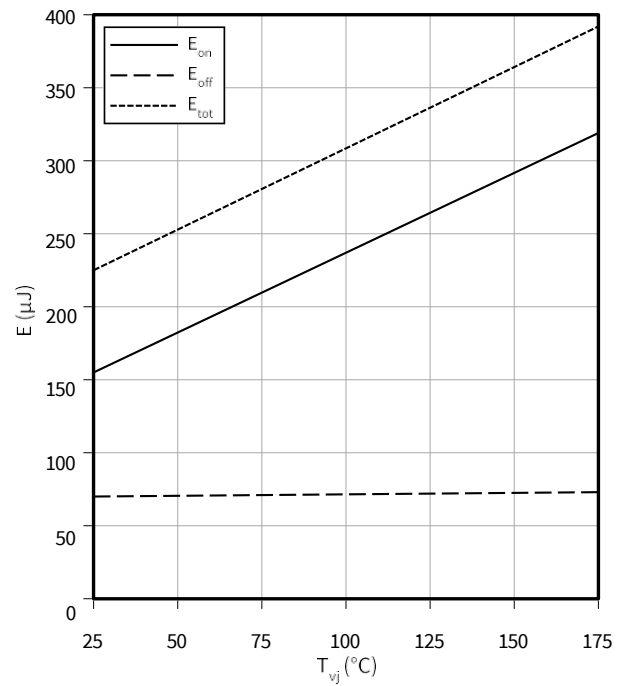
Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 175 \text{ }^\circ\text{C}, t_p = 20 \text{ }\mu\text{s}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0 \text{ V}$

$E = f(T_{vj})$
 $V_{GS} = 0/20 \text{ V}, I_D = 27 \text{ A}, R_{G,ext} = 2 \text{ }\Omega, V_{DD} = 800 \text{ V}$

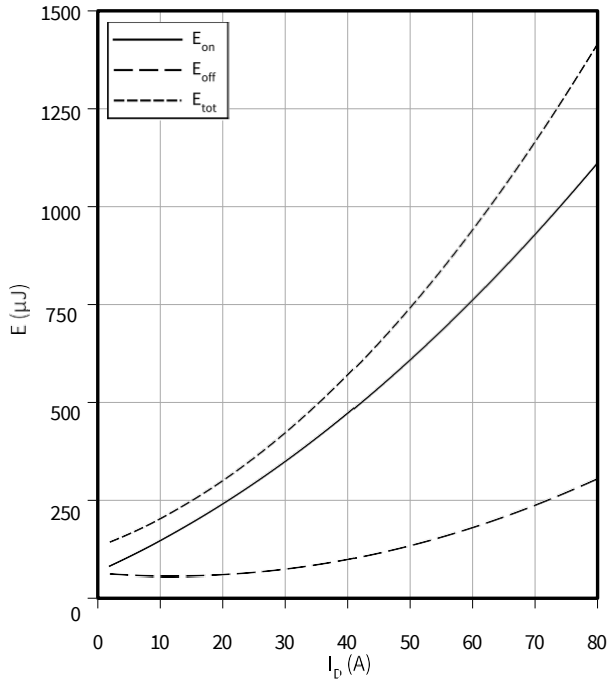


4 特性图

Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$E = f(I_D)$

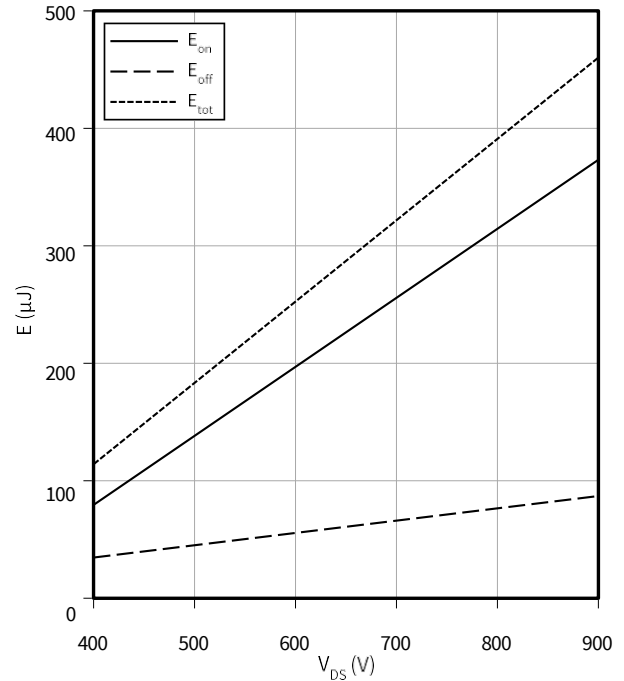
$V_{GS} = 0/20$ V, $T_{vj} = 175$ °C, $R_{G,ext} = 2$ Ω , $V_{DD} = 800$ V



Typical switching energy as a function of drain voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$E = f(V_{DS})$

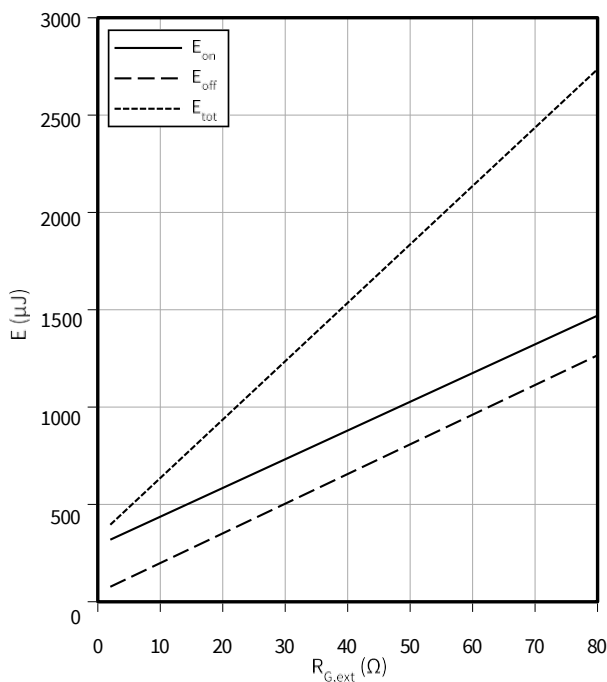
$V_{GS} = 0/20$ V, $I_D = 27$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2$ Ω



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$E = f(R_{G,ext})$

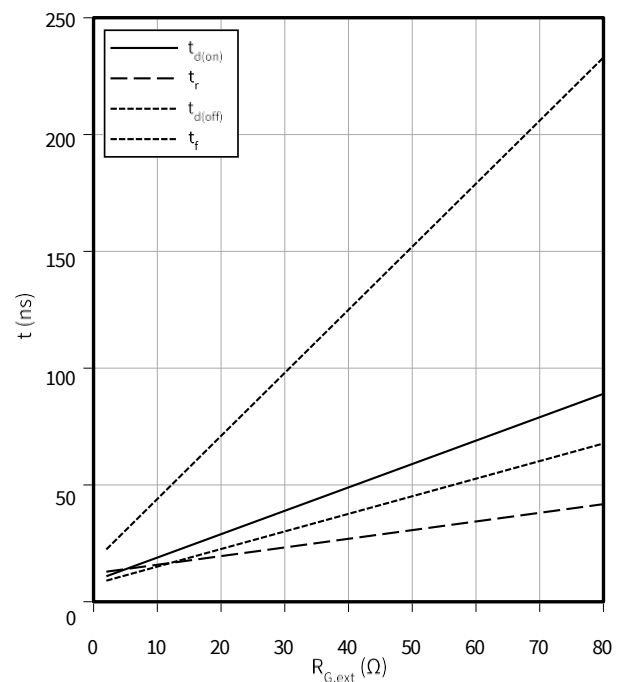
$V_{GS} = 0/20$ V, $I_D = 27$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$t = f(R_{G,ext})$

$V_{GS} = 0/20$ V, $I_D = 27$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V

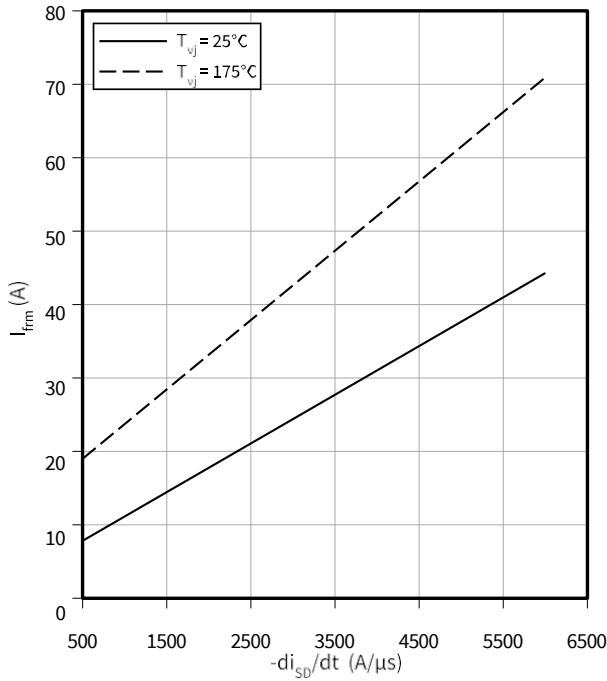


4 特性图

Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$$I_{frm} = f(-di_{SD}/dt)$$

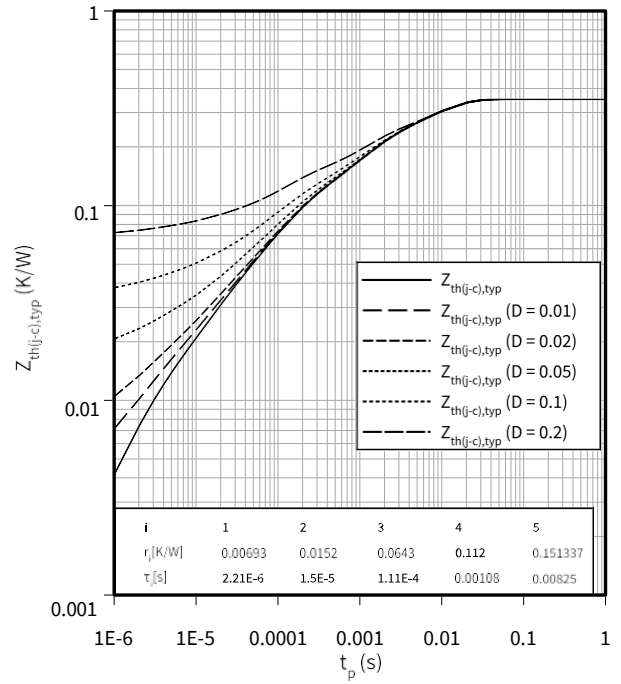
$V_{GS} = 0/20\text{ V}$, $I_{SD} = 27\text{ A}$, $V_{DD} = 800\text{ V}$



Typ. transient thermal impedance (MOSFET/diode)

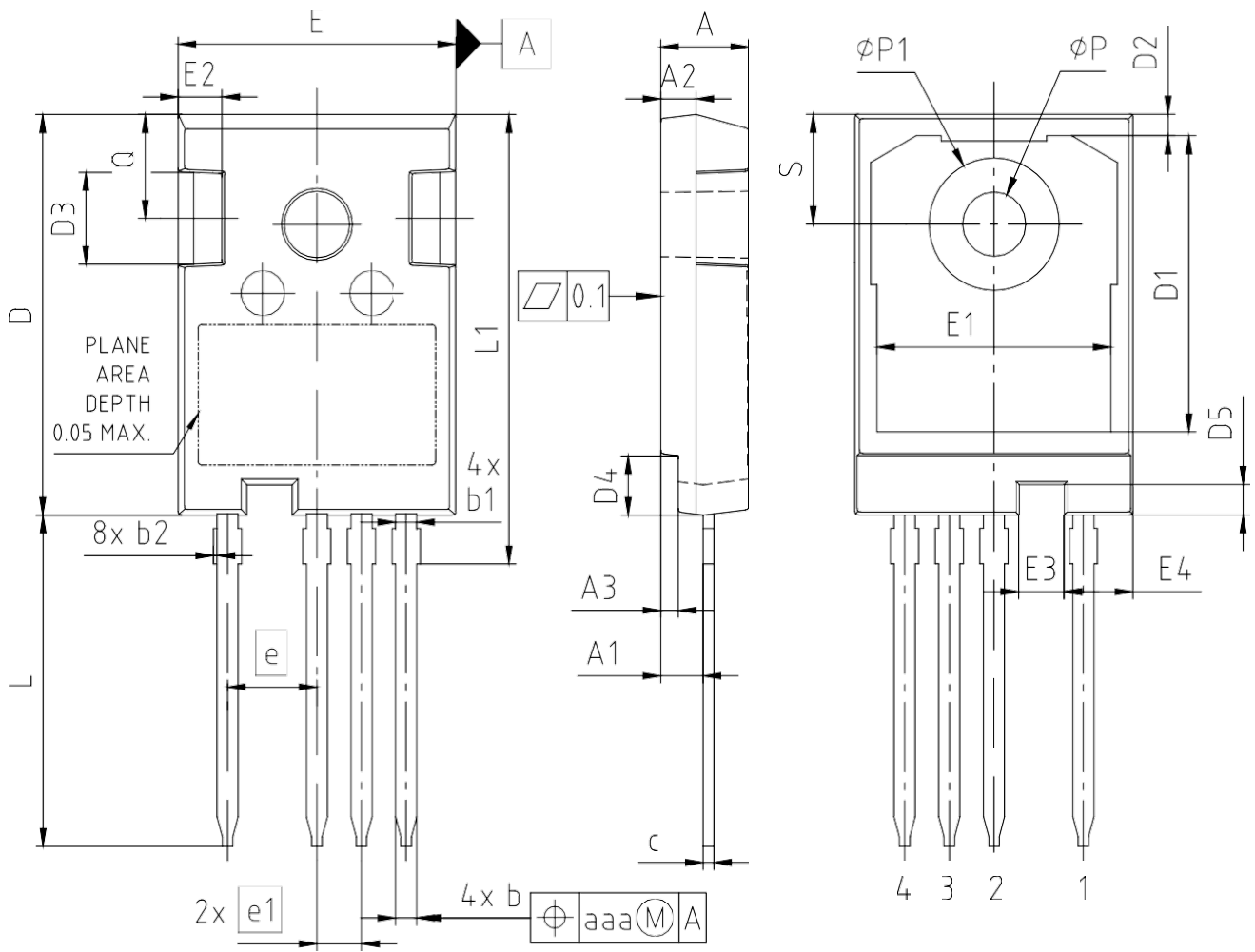
$$Z_{th(j-c),typ} = f(t_p)$$

$$D = t_p/T$$



5 封装外形

5 封装外形



PACKAGE - GROUP NUMBER: PG-T0247-4-U05					
DIMENSIONS	MILLIMETERS		DIMENSIONS	MILLIMETERS	
	MIN.	MAX.		MIN.	MAX.
A	4.90	5.10	E	15.70	15.90
A1	2.31	2.51	E1	13.10	13.50
A2	1.90	2.10	E2	2.40	2.60
A3	0.90	1.10	E3	2.48	2.68
b	1.16	1.29	E4	3.82	4.02
b1	1.16	1.29	e	5.08	
b2		0.20	e1	2.54	
c	0.59	0.66	N	4	
D	22.30	22.50	L	18.40	18.70
D1	16.25	16.85	L1	24.97	25.27
D2	1.05	1.35	phi P	3.50	3.70
D3	5.00	5.20	phi P1		7.40
D4	3.22	3.42	Q	5.60	6.00
D5	1.60	1.80	S	6.00	6.30
			aaa	0.25	

NOTE: DIMENSIONS DO NOT INCLUDE MOLDFLASH; PROTRUSION OR GARE BURRS

图 1

6 测试条件

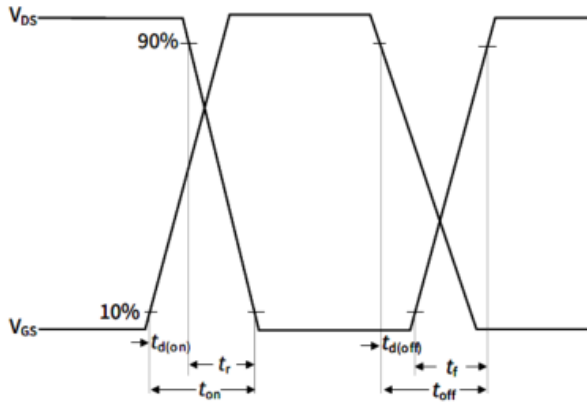


Figure A. Definition of switching times

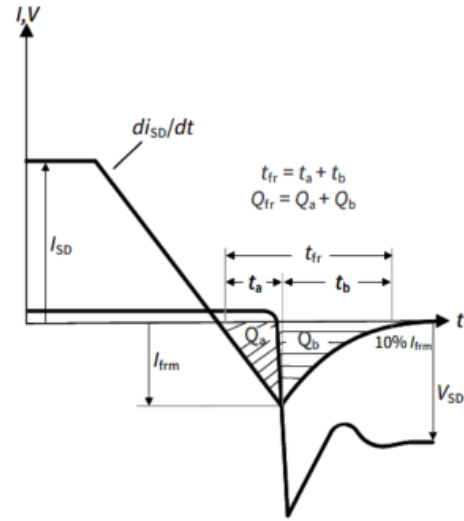


Figure B. Definition of body diode switching characteristics

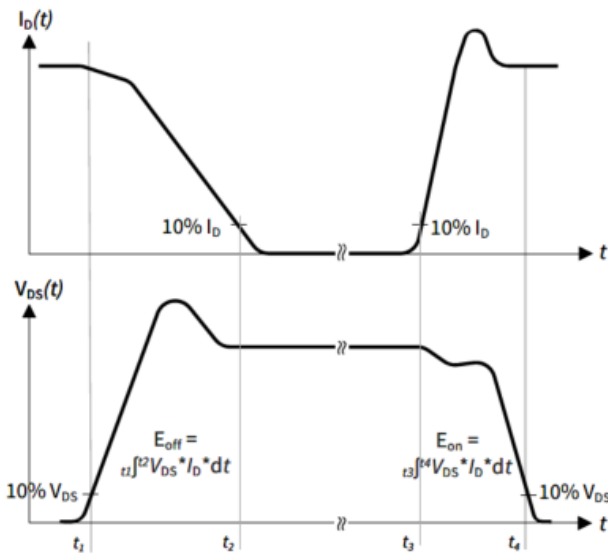


Figure C. Definition of switching losses

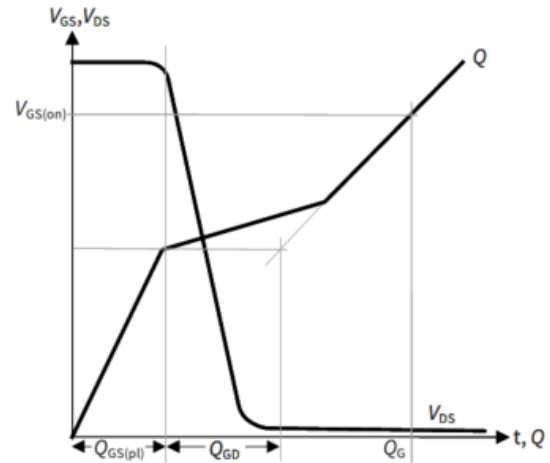


Figure D. Definition of QGD

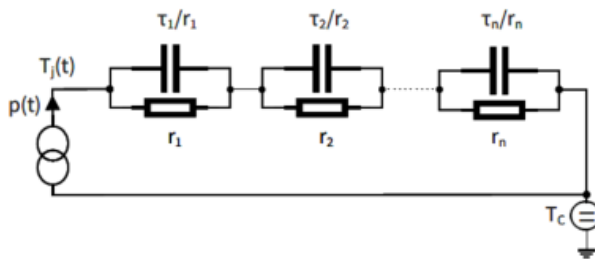


Figure E. Thermal equivalent circuit

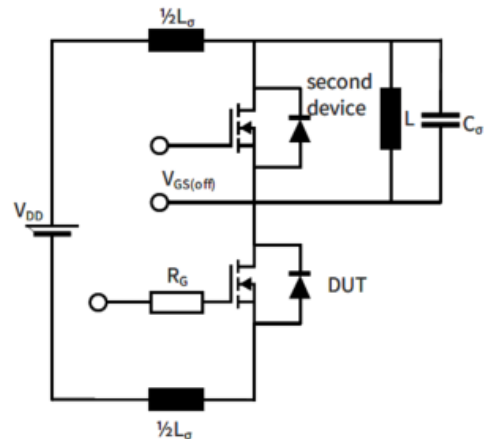


Figure F. Dynamic test circuit
Parasitic inductance L_σ ,
Parasitic capacitor C_σ ,

修订记录

修订记录

Document revision	Date of release	Description of changes
0.10	2022-04-19	Target datasheet
0.20	2023-08-03	Preliminary datasheet
1.00	2023-12-01	Final datasheet
1.10	2025-10-15	<p>Updated table values: g_{fs}, L_{σ} for switching parameters, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f, E_{on}, E_{off}, E_{tot}, I_{SDC}, Q_{fr}, I_{frm}, condition d_{isd}/dt for Q_{fr} and I_{frm}</p> <p>Added values: creepage distance value on p.1, I_{sm} values for limited t_p</p> <p>Updated graphs: $I_{DS} = f(V_{DS})$, $R_{on}(T_{vj})$, $I_{DS}(V_{GS})$, $I_{SD} = f(V_{SD})$, $E = f(T_{vj})$, $E = f(RG_{ext})$, $E = f(I_D)$, $t_{sw} = f(RG_{ext})$, $Z_{th(j-c)} = f(t_p)$</p> <p>Added graphs: $E_{sw} = f(V_{DS})$, $I_{frm} = f(di/dt)$</p> <p>No change to the product, new/added values are based on additional assessments</p>



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版本 2026-03-30

Infineon Technologies AG 出版，
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